2500Vrms

9.2 mm x 10.4 mm x 2.4 mm



**Gate Driver Providing Galvanic isolation Series** 

# Isolation voltage 2500Vrms 1ch Gate Driver Providing Galvanic Isolation

**Key Specifications** 

SSOP-B28W

Isolation Voltage:

## BM60054FV-C

### **General Description**

The BM60054FV-C is a gate driver with isolation voltage 2500Vrms, I/O delay time of 110ns, and a minimum input pulse width of 90ns. Fault signal output function, ready signal output function, under voltage lockout (UVLO) function, short current protection (SCP) function, and switching controller function are all built-in.

#### **Features**

- Provides Galvanic Isolation
- Fault Signal Output Function
- Ready Signal Output Function
- Under Voltage Lockout Function
- Short Circuit Protection Function
- Soft Turn-Off Function for Short Circuit Protection (Adjustable Turn-OFF time)
- Thermal Protection Function
- Active Miller Clamping
- **Switching Controller Function**
- Output State Feedback Function
- UL1577 Recognized:File No. E356010
- AEC-Q100 Qualified(Note 1) (Note 1:Grade1)

#### **Applications**

- **Driving IGBT Gate**
- Driving MOSFET Gate

#### 20V(Max) Maximum Gate Drive Voltage: I/O Delay Time: 110ns(Max) Minimum Input Pulse Width: 90ns(Max) **Package** $W(Typ) \times D(Typ) \times H(Max)$

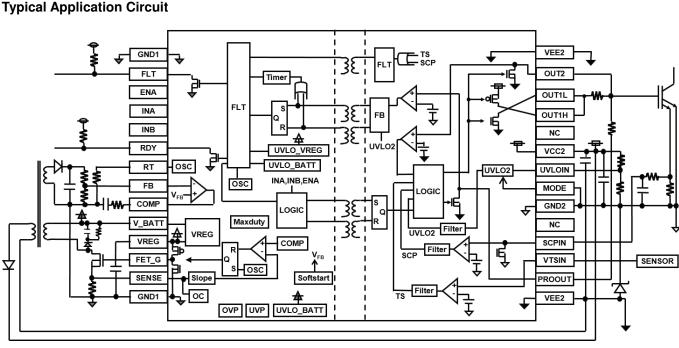


Figure 1. Typical Application Circuit

OProduct structure: Silicon integrated circuit OThis product has no designed protection against radioactive rays

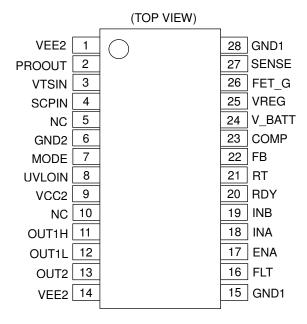
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# **Recommended Range of External Constants**

Pin Name	Name Symbol Recommended			Value	Unit
Fill Name	Symbol	Min	Тур	Max	Ullit
VREG	CVREG	1.0	3.3	10.0	μF
VCC2	Cvcc2	0.33	-	-	μF
RT	R <sub>RT</sub>	24	68	150	kΩ

# **Pin Configuration**



# **Pin Descriptions**

10115		
	Pin Name	Pin Function
1	VEE2	Output-side negative power supply pin
2	PROOUT	Soft turn-off pin / Gate voltage input pin
3	VTSIN	Thermal detection pin
4	SCPIN	Short circuit current detection pin
5	NC	No connection
6	GND2	Output-side ground pin
7	MODE	Mode selection pin of output-side UVLO
8	UVLOIN	Output-side UVLO setting pin
9	VCC2	Output-side positive power supply pin
10	NC	No connection
11	OUT1H	Source side output pin
12	OUT1L	Sink side output pin
13	OUT2	Output pin for Miller Clamp
14	VEE2	Output-side negative power supply pin
15	GND1	Input-side ground pin
16	FLT	Fault output pin
17	ENA	Input enabling signal pin
18	INA	Control input pin A
19	INB	Control input pin B
20	RDY	Ready output pin
21	RT	Switching frequency setting pin for switching controller
22	FB	Error amplifier inverting input pin for switching controller
23	COMP	Error amplifier output pin for switching controller
24	V_BATT	Main power supply pin
25	VREG	Input-side internal power supply pin
26	FET_G	MOS FET control pin for switching controller
27	SENSE	Current detection pin for switching controller
28	GND1	Input-side ground pin

# **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Main Power Supply Voltage	V <sub>BATT</sub>	-0.3 to +40.0 <sup>(Note 2)</sup>	V
Output-Side Positive Supply Voltage	V <sub>CC2</sub>	-0.3 to +24.0 <sup>(Note 3)</sup>	V
Output-Side Negative Supply Voltage	V <sub>EE2</sub>	-15.0 to +0.3 <sup>(Note 3)</sup>	V
Maximum Difference Between Output-Side Positive and Negative Voltages	V <sub>MAX2</sub>	30.0	V
INA, INB, ENA Pin Input Voltage	VIN	-0.3 to +7.0 <sup>(Note 2)</sup>	V
MODE Pin Input Voltage	V <sub>MODE</sub>	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	٧
SCPIN Pin Input Voltage	V <sub>SCPIN</sub>	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
VTSIN Pin Input Voltage	V <sub>VTS</sub>	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
UVLOIN Pin Input Voltage	V <sub>UVLOIN</sub>	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
OUT1H, OUT1L Pin Output Current (Peak 10µs)	I <sub>OUT1PEAK</sub>	5.0 <sup>(Note 4)</sup>	Α
OUT2 Pin Output Current (Peak 10µs)	I <sub>OUT2PEAK</sub>	5.0 <sup>(Note 4)</sup>	Α
PROOUT Pin Output Current (Peak 10µs)	IPROOUTPEA	2.5 <sup>(Note 4)</sup>	Α
FLT, RDY Pin Output Current	I <sub>FLT</sub>	10	mA
FET_G Pin Output Current (Peak 1µs)	FET_GPEAK	1	Α
Power Dissipation	Pd	1.12 <sup>(Note 5)</sup>	W
Operating Temperature Range	Topr	-40 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Junction Temperature	Tjmax	+150	°C

<sup>(</sup>Note 2) Relative to GND1

(Note 5) Derate above Ta=25°C at a rate of 9.5mW/°C. Mounted on a glass epoxy of 70 mm × 70 mm × 1.6 mm

Caution: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

# **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
Main Power Supply Voltage <sup>(Note 6)</sup>	V <sub>BATT</sub>	4.0	32	V
Output-Side Positive Supply Voltage <sup>(Note 7)</sup>	V <sub>CC2</sub>	10	20	V
Output-Side Negative Supply Voltage <sup>(Note 7)</sup>	V <sub>EE2</sub>	-12	0	V
Maximum Difference Between Output-Side Positive and Negative Voltages	V <sub>MAX2</sub>	10	28	V
Switching frequency for switching controller	fswR	100	500	kHz

(Note 6) Relative to GND1 (Note 7) Relative to GND2

**Insulation Related Characteristics (UL1577)** 

Parameter	Symbol	Characteristic	Unit
Insulation Resistance (V <sub>IO</sub> =500V)	Rs	>10 <sup>9</sup>	Ω
Insulation Withstand Voltage / 1min	V <sub>ISO</sub>	2500	Vrms
Insulation Test Voltage / 1sec	V <sub>ISO</sub>	3000	Vrms

<sup>(</sup>Note 3) Relative to GND2

<sup>(</sup>Note 4) Should not exceed Pd and Tj=150°C

# **Electrical Characteristics**

(Unless otherwise specified Ta=-40°C to +125°C, VBATT=4.0V to 32V, VCC2=UVLO to 20V, VEE2=-12V to 0V)

(Unless otherwise specified Ta=	Symbol	Min	Typ	Max	Unit	Conditions
General	Symbol	IVIIII	тур	IVIAX	Offic	Conditions
Main Power Supply						
Circuit Current 1	I <sub>BATT1</sub>	1.1	1.6	2.1	mA	V_BATT=4.0V
Main Power Supply Circuit Current 2	I <sub>BATT2</sub>	0.8	1.3	1.8	mA	V_BATT=12.0V
Main Power Supply						
Circuit Current 3	I <sub>BATT3</sub>	0.8	1.3	1.8	mA	V_BATT=32.0V
Output Side Circuit Current 1	I <sub>CC21</sub>	0.7	1.4	2.1	mA	V <sub>CC2</sub> =14V, OUT1=L
Output Side Circuit Current 2	Icc22	0.4	1.1	1.8	mA	V <sub>CC2</sub> =14V, OUT1=H
Output Side Circuit Current 3	Icc23	0.8	1.5	2.2	mA	Vcc2=18V, OUT1=L
Output Side Circuit Current 4	I <sub>CC24</sub>	0.8	1.2	1.9	mA	V <sub>CC2</sub> =18V, OUT1=H
Output Side Circuit Current 5	ICC25	0.9	1.6	2.3	mA	V <sub>CC2</sub> =16V, V <sub>EE2</sub> =-8V, OUT1=L
Output Side Circuit Current 6	I <sub>CC26</sub>	0.6	1.3	2.0	mA	V <sub>CC2</sub> =16V, V <sub>EE2</sub> =-8V, OUT1=H
Switching Power Supply Control	er					0011-11
						4.2V <v_batt≤32v< td=""></v_batt≤32v<>
FET_G Output Voltage H1	V <sub>FETGH1</sub>	3.8	4.0	4.2	V	I <sub>FET_G</sub> =0A(open)
						V BATT ≤ 4.2V
FET_G Output Voltage H2	V <sub>FETGH2</sub>	-	V_BATT-0.2	V_BATT	V	I <sub>FET_G</sub> =0A(open)
FET_G Output Voltage L	V <sub>FETGL</sub>	0	-	0.3	V	I <sub>FET_G</sub> =0A(open)
FET_G ON-Resistance		0	0	10	•	
(Source-side)	Rongh	3	6	12	Ω	10mA
FET_G ON-Resistance	Rongl	0.3	0.6	1.3	Ω	10mA
(Sink-side)	HONGL	0.3	0.0	1.3	12	TOTILA
Oscillation Frequency	fsw	182	200	222	kHz	RT=68kΩ
Soft-start Time	tss	-	-	50	ms	
FB Pin Threshold Voltage	$V_{FB}$	1.47	1.50	1.53	V	
FB Pin Input Current	I <sub>FB</sub>	-0.8	0	0.8	μΑ	
COMP Pin Sink Current	ICOMPSINK	-160	-80	-40	μΑ	
COMP Pin Source Current	I <sub>COMPSOURCE</sub>	40	80	160	μΑ	
V_BATT UVLO ON Voltage	VUVLOBATTL	3.20	3.40	3.60	V	
V_BATT UVLO Hysteresis	V <sub>UVLOBATTHYS</sub>	0.07	0.1	0.13	V	
Maximum ON DUTY	DONMAX		48	_	%	
Over Voltage Detection Threshold	Vovth	1.60	1.65	1.70	V	
Under Voltage Detection Threshold	V <sub>UVTH</sub>	1.23	1.30	1.37	٧	
Over-Current Detection Threshold	Vостн	0.17	0.20	0.23	V	
Protection Holding Time	tDCDCRLS	20	40	60	ms	
Logic Block						•
Logic High Level Input Voltage	V <sub>INH</sub>	2.0	-	5.5	V	INA, INB, ENA
Logic Low Level Input Voltage	V <sub>INL</sub>	0	-	0.8	V	INA, INB, ENA
Logic Pull-Down Resistance	RIND	25	50	100	kΩ	INA, INB, ENA
Logic Input Filtering Time	tinfil	-	-	90	ns	INA, INB
ENA Input Filtering Time	tenafil	-	0.5	0.8	μs	ENA
MODE Low Level Input Voltage	V <sub>MODEL</sub>	0	-	0.3×V <sub>CC2</sub>	V	MODE, relative to GND2
MODE High Level Input Voltage	V <sub>MODEH</sub>	0.7×V <sub>CC2</sub>	-	V <sub>CC2</sub>	V	MODE,relative to GND2

# **Electrical Characteristics – continued**

(Unless otherwise specified Ta=-40°C to +125°C, VBATT=4.0V to 32V, VCC2=UVLO to 20V, VEE2=-12V to 0V)

Output         Output OUTH ON-Resistance         Ronet         0.50         0.85         1.45         Ω         lourne=40mA           OUTH ON-Resistance         Ronit         0.25         0.45         0.80         Ω         lourne=40mA           OUT1 Maximum Current         Iourne=40mA         3.0         4.5         -         A         Design assurance           PROOUT ON-Resistance         Rowero         0.45         0.85         1.55         Ω         leroout=40mA           Turn ON Time         Icona         45         75         105         ns         INA=PWM, INB=L           Turn ON Time         Icona         45         75         105         ns         INA=PWM, INB=L           Turn OFF Time         Icona         40         70         100         ns         INA=PWM, INB=L           Turn OFF Time         Icona         15         5         15         ns         InA=PWM, INB=L           Turn OFF Time         Icona         15         65         95         ns         INA=PWM, INB=L           Turn OFF Time         Icona         15         ns         15         ns         InDepts InBPWM           Turn OFF Time         Icona         15         ns         15	Parameter	Symbol	Min	Typ	Max	Unit	Conditions
OUT1H ON-Resistance		Cymbol	101111	1 170	IVIQX	Onit	Conditions
OUT1L ON-Resistance	•	RONH	0.50	0.85	1 45	0	IOUT1H=40mA
OUT1 Maximum Current   IouTHMAX   3.0   4.5   -							
PROOUT ON-Resistance   Rowerd   Rowe			3.0	4.5	-	А	V <sub>CC2</sub> =15V
Turn ON Time	PROOUT ON-Resistance	Ronpro	0.45	0.85	1.55	Ω	
Turn OFF Time		tpona	45	75	105	ns	INA=PWM, INB=L
Turn OFF Time	Turn ON Time	tponb	50	80	110	ns	INA=H, INB=PWM
Troperation	T 055 T	tpoffa	40	70	100	ns	INA=PWM, INB=L
Propagation Distortion   Itenistra   -35   -15   5   ns   Incepta   -160NB	Turn OFF Time	tроггв	35	65	95	ns	INA=H, INB=PWM
Froistre   1505   15   5   18   1507679   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   17070   1	D .: D: . ::	t <sub>PDISTA</sub>	-25	-5	15	ns	tpoffa – tpona
Fall Time	Propagation Distortion	tрыsтв	-35	-15	5	ns	tpoffb - tponb
OUT2 ON-Resistance         Ronz         0.25         0.45         0.80         Ω         lourz=40mA           OUT2 ON Threshold Voltage         Voutzon         1.8         2         2.2         V         Relative to VEE2           Common Mode Transient Immunity         CM         100         -         -         kV/µs         Design assurance           Protection Functions           Output-side UVLO ON           Threshold Voltage         VuVLOINL         0.85         0.90         0.95         V         UVLOIN, MODE=L           Output-side UVLO Threshold Hysteresis         VuVLOINL         VUVLOINL <td< td=""><td>Rise Time</td><td>t<sub>RISE</sub></td><td>-</td><td>50</td><td>-</td><td>ns</td><td>10nF between OUT1-VEE2</td></td<>	Rise Time	t <sub>RISE</sub>	-	50	-	ns	10nF between OUT1-VEE2
OUT2 ON Threshold Voltage	Fall Time	<b>t</b> FALL	-	50	-	ns	Design assurance
Common Mode Transient Immunity   CM   100   -   -   kV/μs   Design assurance	OUT2 ON-Resistance	R <sub>ON2</sub>	0.25	0.45	0.80	Ω	I <sub>OUT2</sub> =40mA
Protection Functions	OUT2 ON Threshold Voltage	V <sub>OUT2ON</sub>	1.8	2	2.2	V	Relative to VEE2
Output-side UVLO ON Threshold Voltage         VuvLoINL VuVLOINL         0.85         0.90         0.95         V         UVLOIN, MODE=L           Output-side UVLO Threshold Hysteresis         VuVLOINL VuVLOINL         0.11× VuVLOINL VuVLOINL         V         UVLOIN, MODE=L           Output-side UVLO ON Voltage Output-side UVLO Hysteresis         VuVLOZEL VUVLOZEL         10.9         11.5         12.1         V         VCC2, MODE=H           Output-side UVLO Hysteresis Output-side UVLO Filtering Time         tuvLo2FIL         0.25         1.5         3.7         μs           DESAT Leading Edge Blanking Time         tobsATIeb         0.14         0.20         0.26         μs         Design assurance           Short Current Detection Voltage         VscDET         0.47         0.50         0.53         V         Relative to GND2           Short Current Detection Filter Time         tscPFIL         0.12         0.2         0.28         μs           Short Current Detection Delay Time (PROOUT)         tscPPRO         0.26         0.38         0.50         μs           SCPIN Pin Low Voltage         VscPINL         -         0.1         0.22         V         IscPIN=1mA           Output Delay Difference between PROOUT and FLT         tpROFLT         0.1         0.4         0.7         μs	Common Mode Transient Immunity	СМ	100	-	-	kV/μs	Design assurance
Threshold Voltage	Protection Functions						
Output-side UVLO Threshold         VuVLOINHYS         0.10× VuVLOINL         0.11× VuVLOINL         VUVCOINL         VUCC2, MODE=H         DECT         DECTHOR	•	Vuvloinl	0.85	0.90	0.95	V	UVLOIN, MODE=L
Hysteresis	Output-side UVLO Threshold	VIIVI OINIHVS	0.10×	0.11×	0.12×	V	UVI OIN, MODE=I
Output-side UVLO Hysteresis         VuvLozhys         0.8         1.2         1.6         V         VCC2, MODE=H           Output-side UVLO Filtering Time         tuvLozfill         0.25         1.5         3.7         μs         DESAT Leading Edge           Blanking Time         tobsatieb         0.14         0.20         0.26         μs         Design assurance           Short Current Detection Voltage         VscDET         0.47         0.50         0.53         V         Relative to GND2           Short Current Detection Filter Time         tscPPRO         0.12         0.2         0.28         μs           Short Current Detection Delay Time (PROOUT)         tscPPRO         0.26         0.38         0.50         μs           SCPIN Pin Low Voltage         VscPINL         -         0.1         0.22         V         IscPIN=1mA           Output Delay Difference between PROOUT and FLT         tpROFLT         0.1         0.4         0.7         μs         Parameter Time         translate to GND2           Thermal Detection Voltage         Vsbett         4         10         30         μs           Soft Turn Off Release Time         tsto         30         -         110         μs           FLT Output Low Voltage         Vs	•	VOVEOINHTS	$V_{\text{UVLOINL}}$	V <sub>UVLOINL</sub>	V <sub>UVLOINL</sub>	•	
Output-side UVLO Filtering Time         tuvLo2FIL         0.25         1.5         3.7         μs           DESAT Leading Edge Blanking Time         tDESATIeb         0.14         0.20         0.26         μs         Design assurance           Short Current Detection Voltage         VSCDET         0.47         0.50         0.53         V         Relative to GND2           Short Current Detection Filter Time         tscPFIL         0.12         0.2         0.28         μs           Short Current Detection Delay Time (PROOUT)         tscPPRO         0.26         0.38         0.50         μs           SCPIN Pin Low Voltage         VSCPINL         -         0.1         0.22         V         IscPIN=1mA           Output Delay Difference Detween PROOUT and FLT         tPROFLT         0.1         0.4         0.7         μs           Thermal Detection Voltage         VTSDET         1.61         1.70         1.79         V         Relative to GND2           Thermal Detection Filter Time         tsto         30         -         110         μs           Soft Turn Off Release Time         tsto         30         -         110         μs           FLT Output Low Voltage         VFLTL         -         0.18         0.40	Output-side UVLO ON Voltage		10.9		12.1	<u> </u>	-
DESAT Leading Edge   Blanking Time   Design assurance   Design assurance   Desatieb   Design assurance   Desatieb   Design assurance   Design a	•	V <sub>UVLO2HYS</sub>		<b>+</b>	<u> </u>	V	VCC2, MODE=H
Blanking Time	Output-side UVLO Filtering Time	tuvlo2fil	0.25	1.5	3.7	μs	
Short Current Detection Filter Time   tscpfil   0.12   0.2   0.28   μs		t <sub>DESATIeb</sub>	0.14	0.20	0.26	μs	Design assurance
Short Current Detection Delay Time (PROOUT)   tscppro   0.26   0.38   0.50   μs	Short Current Detection Voltage	V <sub>SCDET</sub>	0.47	0.50	0.53	V	Relative to GND2
Time (PROOUT)   TSCPPRO   0.26   0.38   0.50   μs	Short Current Detection Filter Time	tscpfil	0.12	0.2	0.28	μs	
SCPIN Pin Low Voltage       V <sub>SCPINL</sub> -       0.1       0.22       V       I <sub>SCPIN</sub> =1mA         Output Delay Difference between PROOUT and FLT       tPROFLT       0.1       0.4       0.7       μs         Thermal Detection Voltage       VTSDET       1.61       1.70       1.79       V       Relative to GND2         Thermal Detection Filter Time       tTSFIL       4       10       30       μs         Soft Turn Off Release Time       tSTO       30       -       110       μs         FLT Output Low Voltage       VFLTL       -       0.18       0.40       V       I <sub>FLT</sub> =5mA         Gate State H Detection Threshold Voltage       VOSFBH       4.5       5.0       5.5       V       Relative to GND2         Gate State L Detection Threshold Voltage       VOSFBL       4.0       4.5       5.0       V       Relative to GND2         OSFB Output Filtering Time       tosfbfil       1.5       2.0       2.5       μs		tscppro	0.26	0.38	0.50	μs	
Output Delay Difference between PROOUT and FLTtpROFLT0.10.40.7μsThermal Detection VoltageVTSDET1.611.701.79VRelative to GND2Thermal Detection Filter TimetTSFIL41030μsSoft Turn Off Release TimetSTO30-110μsFLT Output Low VoltageVFLTL-0.180.40VIFLT=5mAGate State H Detection Threshold VoltageVOSFBH4.55.05.5VRelative to GND2Gate State L Detection Threshold VoltageVOSFBL4.04.55.0VRelative to GND2OSFB Output Filtering Timetosfbfill1.52.02.5μs	,	VSCPINI	-	0.1	0.22	V	Iscein=1mA
Thermal Detection Voltage VTSDET 1.61 1.70 1.79 V Relative to GND2 Thermal Detection Filter Time tsto 30 - 110 μs  Soft Turn Off Release Time tsto 30 - 110 μs  FLT Output Low Voltage VFLTL - 0.18 0.40 V IFLT=5mA  Gate State H Detection Threshold Voltage VOSFBH VOSFBH 4.5 5.0 5.5 V Relative to GND2  Gate State L Detection Threshold Voltage VOSFBL 4.0 4.5 5.0 V Relative to GND2  OSFB Output Filtering Time tosfbfil 1.5 2.0 2.5 μs	Output Delay Difference		0.1				000
Thermal Detection Filter Time   t <sub>TSFIL</sub>   4   10   30   μs		VTSDET	1,61	1.70	1.79	V	Relative to GND2
Soft Turn Off Release Time   tsτo   30   -   110   μs     FLT Output Low Voltage   V <sub>FLTL</sub>   -   0.18   0.40   V   I <sub>FLT</sub> =5mA     Gate State H Detection   Threshold Voltage   V <sub>OSFBH</sub>   4.5   5.0   5.5   V   Relative to GND2     Gate State L Detection   Threshold Voltage   V <sub>OSFBL</sub>   4.0   4.5   5.0   V   Relative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   μs   Elative to GND2     OSFB Output Filtering Time   tosfbfil   1.5   2.0   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5   2.5				†	1		2.3
FLT Output Low Voltage V <sub>FLTL</sub> - 0.18 0.40 V I <sub>FLT</sub> =5mA  Gate State H Detection Threshold Voltage V <sub>OSFBH</sub> 4.5 5.0 5.5 V Relative to GND2  Gate State L Detection Threshold Voltage V <sub>OSFBL</sub> 4.0 4.5 5.0 V Relative to GND2  OSFB Output Filtering Time tosfbfil 1.5 2.0 2.5 µs				-			
Gate State H Detection     VOSFBH     4.5     5.0     5.5     V     Relative to GND2       Threshold Voltage     VOSFBL     4.0     4.5     5.0     V     Relative to GND2       OSFB Output Filtering Time     tosfbfil     1.5     2.0     2.5     μs			-	0.18		-	I <sub>FIT</sub> =5mA
Gate State L Detection Threshold Voltage  OSFB Output Filtering Time  VosFBL  VosFBL  4.0  4.5  5.0  V Relative to GND2  DSFB Output Filtering Time  VosFBFIL  1.5  2.0  2.5  μs	Gate State H Detection		4.5				
OSFB Output Filtering Time tosfbfil 1.5 2.0 2.5 µs	Gate State L Detection	Vosfbl	4.0	4.5	5.0	V	Relative to GND2
		tosereii	1.5	2.0	2.5	us	
TID I CUIDULEON VOILUUG VEDTI - U.TO U.HU V TERTYETIIIA	RDY Output Low Voltage	V <sub>RDYL</sub>	-	0.18	0.40	V	I <sub>RDY</sub> =5mA

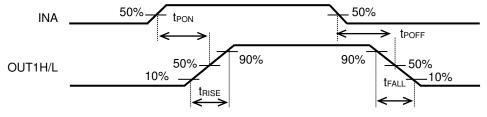


Figure 2. INA-OUT1H/L Timing Chart

# **UL1577 Ratings Table**

Following values are described in UL Report.

Parameter	Values	Units	Conditions
Side 1 (Input Side) Circuit Current	1.3	mA	V_BATT=12V, OUT1H/L=L
Side 2 (Output Side) Circuit Current	1.6	mA	VCC2=18V, VEE2=-6V, OUT1H/L=L
Side 1 (Input Side) Consumption Power	15.6	mW	V_BATT=12V, OUT1H/L=L
Side 2 (Output Side) Consumption Power	38.4	mW	VCC2=18V, VEE2=-6V, OUT1H/L=L
Isolation Voltage	2500	Vrms	
Maximum Operating (Ambient) Temperature	125	°C	
Maximum Junction Temperature	150	°C	
Maximum Strage Temperature	150	°C	
Maximum Data Transmission Rate	5.5	MHz	

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# **Typical Performance Curves**

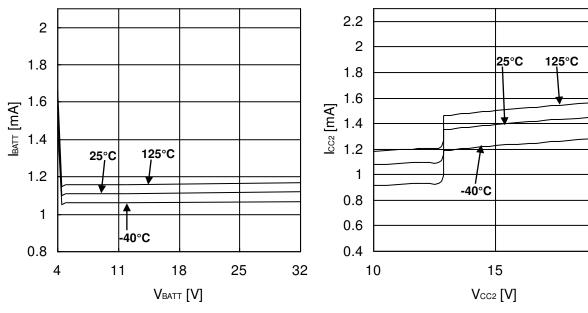


Figure 3. Main Power Supply Circuit Current

Figure 4. Output Side Circuit Current (MODE=H, VEE2=0V, OUT1=L)

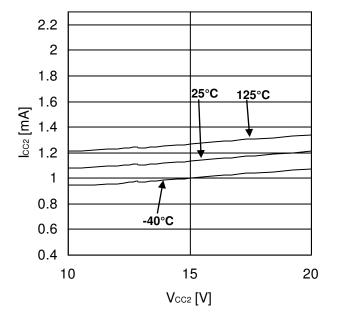


Figure 5. Output Side Circuit Current (MODE=H, VEE2=0V, OUT1=H)

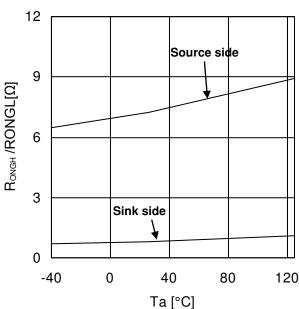


Figure 6. FET\_G ON-Resistance (Source side/Sink side)

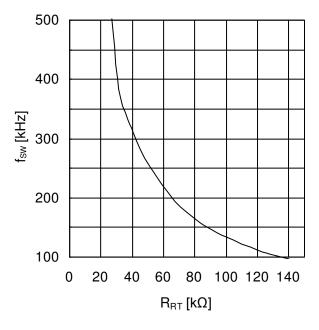


Figure 7. Oscillation Frequency

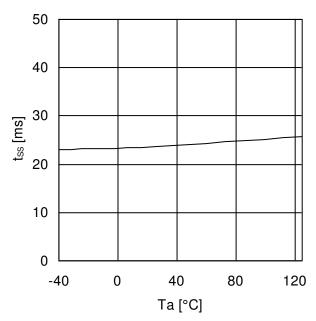


Figure 8. Soft-start Time

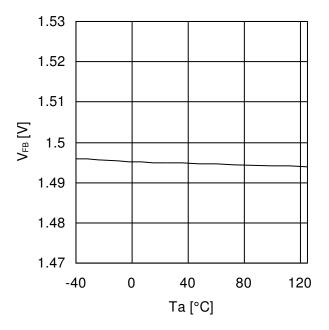


Figure 9. FB Pin Threshold Voltage

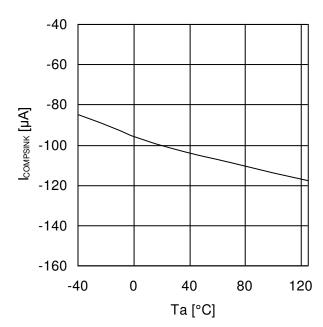


Figure 10. COMP Pin Sink Current

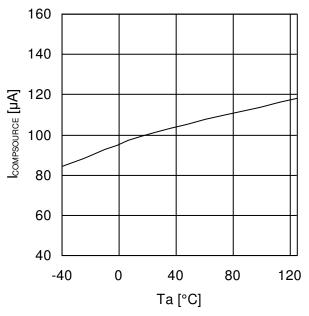


Figure 11. COMP Pin Source Current

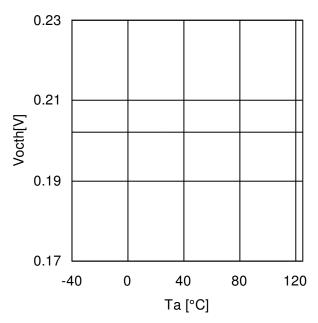


Figure 12. Over-Current Detection Threshold

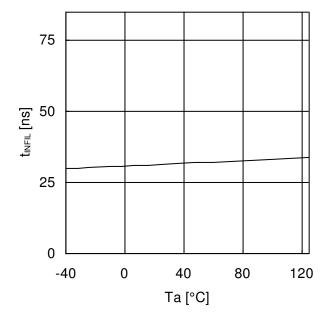


Figure 13. Logic Input Filtering Time (L pulse)

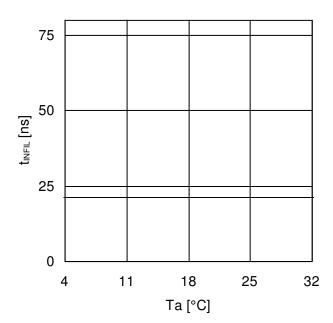


Figure 14. Logic Input Filtering Time (H pulse)

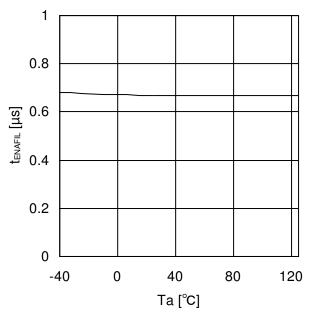


Figure 15. ENA Input Filtering Time

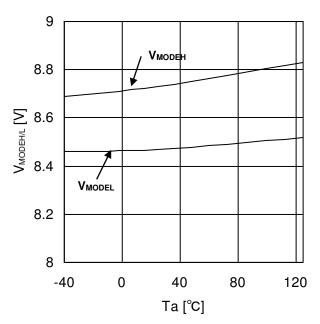


Figure 16. MODE Input Voltage H/L

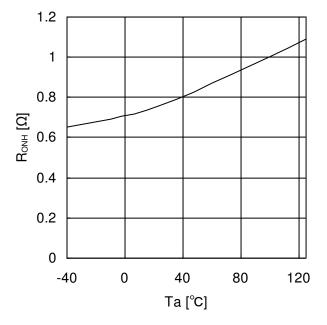


Figure 17. OUT1H ON-Resistance (IOUT1=40mA)

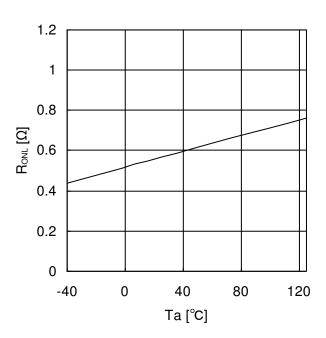


Figure 18. OUT1L ON-Resistance (Iout1=40mA)

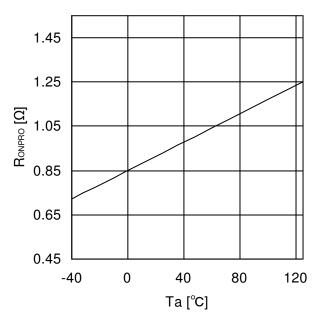


Figure 19. PROOUT ON-Resistance (IPROOUT=40mA)

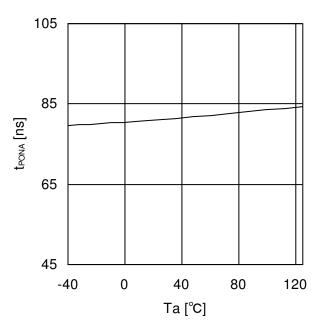


Figure 20. Turn ON time

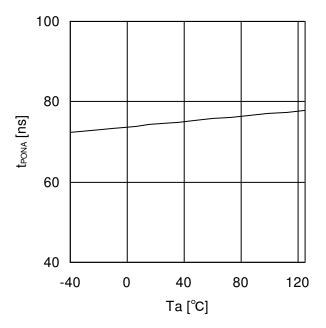


Figure 21. Turn OFF time

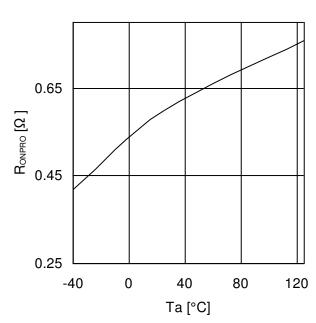
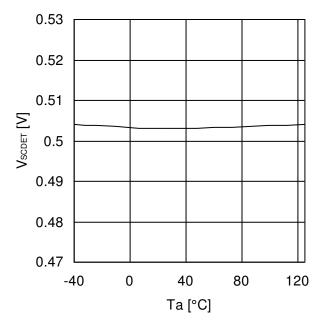


Figure 22. OUT2 ON-Resistance (Iout2=40mA)



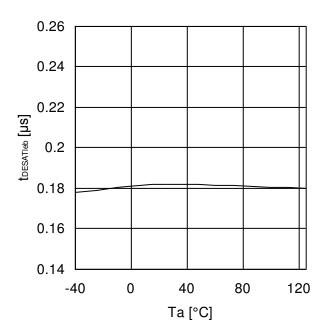


Figure 23. Short Current Detection Voltage

Figure 24. DESAT Leading Edge Blanking Time

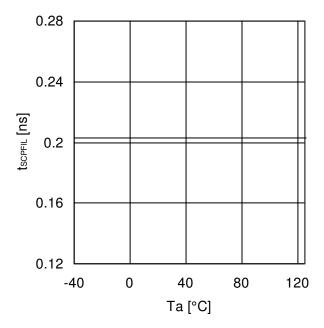


Figure 25. Short Current Detection Filter Time

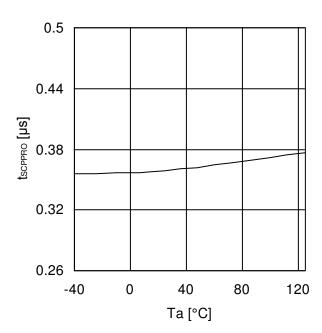
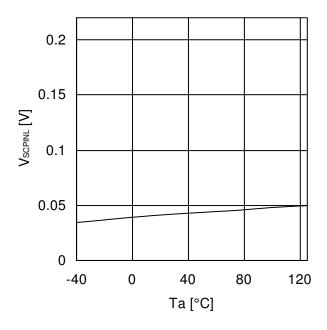


Figure 26. Short Current Detection Delay Time





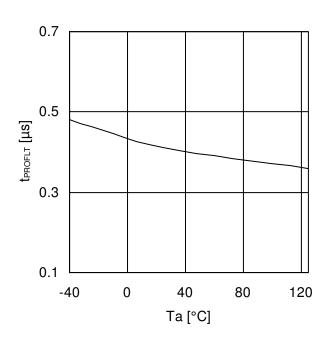


Figure 28. Output Delay Difference between PROOUT and FLT

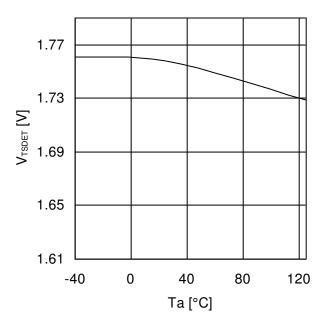


Figure 29. Thermal Detection Voltage

#### **Application Information**

#### 1. Description of Pins and Cautions on Layout of Board

#### (1) V BATT (Main Power Supply Pin)

This is the main power supply pin. Connect a bypass capacitor between V\_BATT and GND1 in order to suppress voltage variations.

#### (2) GND1 (Input-side Ground Pin)

The GND1 pin is a ground pin on the input side.

#### (3) VCC2 (Output-side Positive Power Supply Pin)

The VCC2 pin is a positive power supply pin on the output side. To reduce voltage fluctuations due to OUT1H/L pin output current and due to the driving current of the internal transformers, connect a bypass capacitor between VCC2 and GND2 pins.

#### (4) VEE2 (Output-side Negative Power Supply Pin)

The VEE2 pin is a power supply pin on the output side. To suppress voltage fluctuations due to OUT1H/L pin output current and due to the driving current of the internal transformers, connect a bypass capacitor between the VEE2 and the GND2 pins. Connect the VEE2 pin to the GND2 pin when no negative power supply is used,

#### (5) GND2 (Output-side Ground Pin)

The GND2 pin is a ground pin on the output side. Connect the GND2 pin to the emitter / source of a power device.

#### (6) INA, INB, ENA (Control Input Terminal)

The INA, INB, ENA are pins used to determine output logic.

ENA	INB	INA	OUT1H	OUT1L
L	X	Χ	Hi-Z	L
Н	Н	Χ	Hi-Z	L
Н	L	L	Hi-Z	L
Н	Ĺ	Н	Н	Hi-Z

Fault state(FLT=L output) is released in rising of ENA(L→ H).

#### (7) FLT (Fault Output Pin)

The FLT pin is an open drain pin used to output a fault signal when short circuit protection function (SCP) or thermal protection function is activated, and will be cleared at the rising edge of ENA.

Status FLT

While in normal operation Hi-Z

When a fault occurs
(When SCP or thermal protection is activated)

#### (8) RDY (Ready Output Pin)

The RDY pin shows the status of three internal protection features which are V\_BATT UVLO, VCC2 UVLO, and output state feedback (OSFB). The term 'output state feedback' shows whether PROOUT pin voltage (High or Low) corresponds to input logic or not.

Status	RDY
While in normal operation	Hi-Z
V_BATT UVLO or VCC2 UVLO or Output state feedback	L

#### (9) MODE (Mode Selection Pin of Output-side UVLO)

The MODE pin is a pin which selects internal threshold or external setting threshold for output-side UVLO.

MODE	Output-side UVLO threshold voltage
L (=GND2)	Setting by external. (Use UVLOIN pin)
H (=VCC2)	Fixed (=VuvLo2L). (Connect UVLOIN pin to VCC2 pin)

#### (10) UVLOIN (Output-side UVLO Setting Input Pin)

The UVLOIN pin is a pin for deciding UVLO setting value of VCC2. The threshold value of UVLO can be set by dividing the resistance voltage of VCC2 and inputting such value. UVLOIN activates only at MODE pin=L. When MODE pin=H, connect UVLOIN pin to VCC2 pin.

# (11) OUT1H, OUT1L(Output Pin)

The OUT1H pin is a source side pin used to drive the gate of a power device, and the OUT1L pin is a sink side pin used to drive the gate of a power device.

#### (12) OUT2 (Miller Clamp Pin)

This is the miller clamp pin for preventing a rise of gate voltage due to miller current of output element connected to OUT1. It also functions as a pin for monitoring gate voltage for miller clamp and OUT2 pin voltage become not more than VOUT2ON(typ 2.0V), miller clamp function operates. OUT2 should be connect to VEE2 when miller clamp function is not used.

# (13) PROOUT (Soft Turn-OFF Pin)

This is a pin for soft turn-OFF of output pin when short-circuit protection is in action. It also functions as a pin for monitoring gate voltage for output state feedback function.

#### (14) SCPIN(Short Circuit Current Detection Pin)

The SCPIN pin is a pin used to detect current for short circuit protection. When the SCPIN pin voltage exceeds  $V_{SCDET}$ , SCP function will be activated. This may cause the IC to malfunction in an open state. To avoid such trouble, short-circuit the SCPIN pin to the GND2 pin when the short circuit protection is not used. In order to prevent the wrong detection due to noise, the noise filter time  $t_{SCPFIL}$  is set.

# (15) VTSIN (Thermal Detection Pin)

The VTSIN pin is a temperature sensor voltage input pin, which can be used for thermal protection of an output device. If VTSIN pin voltage becomes  $V_{TSDET}$  or less, OUT1H/L pin is set to HiZ/L. IC may malfunction in the open status, so be sure to supply the VTSPIN more than  $V_{TSDET}$  if the thermal protection function is not used. In order to prevent the wrong detection due to noise, the noise mask time  $t_{TSMSK}$  is set. In addition, it can be used also as compulsive shutdown terminal other than a temperature sense by inputting a comparator output etc.

#### (16) RT (Switching Frequency Setting Pin for Switching Controller)

The RT pin is a pin used to make setting of switching frequency of switching controller. The switching frequency is determined by the resistance value connected between RT and GND1. The value of switching frequency is determined by the value of the resistor  $R_{\rm RT}$ .

$$F_{SW}[kHz] = 1/(7.3 \times 10^{-8} \times R_{RT} + 2.2 \times 10^{-4})$$

#### (17) FB (Error Amplifier Inverting Input Pin for Switching Controller)

This is a voltage feedback pin of the switching controller. This pin combine with voltage monitoring at overvoltage protection function and under voltage protection function for switching controller. When overvoltage or under voltage protection is activated, switching controller will be at OFF state (FET\_G pin outputs Low). When the protection holding time (tDCDCRLS) is completed, the protection function will be released. Under voltage function is not activated during soft-start.

#### (18) COMP (Error Amplifier Output Pin for Switching Controller)

This is the gain control pin of the switching controller. Connect a phase compensation capacitor and resistor.

# (19) VREG (Input-side internal power supply pin)

This is the input-side internal power supply pin. Be sure to connect a capacitor between VREG and GND1 even when the switching controller is not used, in order to prevent oscillation and suppress voltage variation due to FET\_G output current.

#### (20) FET G (MOS FET Control Pin for Switching Controller)

This is a MOSFET control pin for the switching controller transformer drive.

# (21) SENSE (Connection to the Current Feedback Resistor of the Switching Controller)

This is a pin connected to the resistor of the switching controller current feedback. This pin combines with current monitoring at overcurrent protection function for switching controller. When overcurrent protection is activated, switching controller will be at OFF state (FET\_G pin outputs Low). When the protection holding time (tdcdcrls) is completed, the over-current function will be released.

# 2. Description of Functions and Examples of Constant Setting

(1) Miller Clamp Function When OUT1=L and OUT2 pin voltage < V<sub>OUT2ON</sub>, internal MOS of OUT2 pin is turned ON and miller clamp function operates.

IN	OUT2 pin input voltage	OUT2
L	Not more than V <sub>OUT2ON</sub>	L
Н	Х	Hi-Z

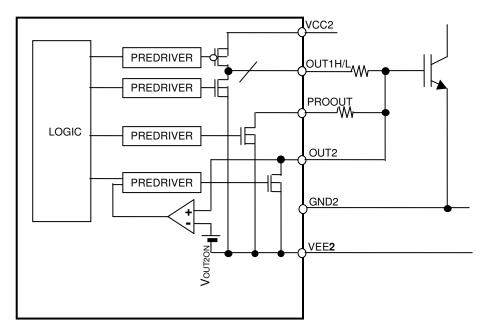


Figure 30. Block Diagram of Miller Clamp Function

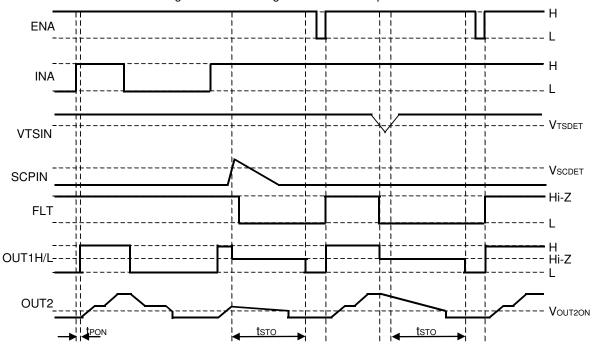


Figure 31. Timing Chart of Miller Clamp Function

(2) Under Voltage Lockout (UVLO) Function

The BM60054FV-C incorporates the under voltage lockout (UVLO) function on V\_BATT and VCC2. When the power supply voltage drops to the UVLO ON voltage, the OUT1H/L pin will output the "Hi-Z / L" and the FLT pin will output the "L" signal. When the power supply voltage rises to the UVLO OFF voltage, these pins will be reset. In addition, to prevent mis-triggers due to noise, mask time tuvlobattfil and tuvlozfil are set on both voltage sides.

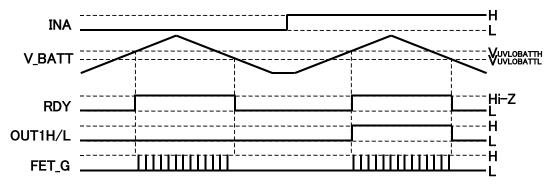


Figure 32. VBATT UVLO Function Operation Timing Chart

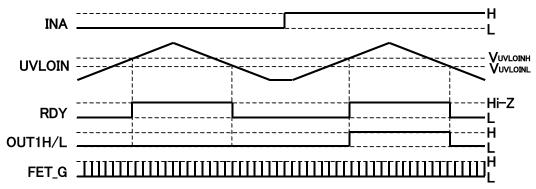


Figure 33. VCC2 UVLO Function Operation Timing Chart (MODE=L)

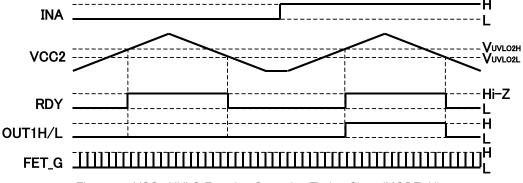


Figure 34. VCC2 UVLO Function Operation Timing Chart (MODE=H)

(3) Short Circuit Protection Function (SCP)

When the SCPIN pin voltage exceeds  $V_{SCDET}$ , the SCP function will be activated. When the SCP function is activated, the OUT1H/L pin voltage will be set to the "Hi-Z/Hi-Z" level and the PROOUT pin voltage will go to the "L" level first (soft turn-OFF). Next, After  $t_{STO}$  has passed, OUT1H/L pin become Hi-Z/L (PROOUT pin hold L). In addition, when OUT2 pin voltage <  $V_{OUT2ON}$ , miller clamp function operates.

When the rising edge is put in the ENA pin, the SCP function will be released.

When OUT1H/L=Hİ-Z/L or Hi-Z/Hi-Z, internal MOSFET connected to SCPIN pin turns ON to discharge C<sub>BLANK</sub> for desaturation protection function. When OUT1H/L=H/Hi-Z, internal MOSFET connected to SCPIN pin turns OFF.

$$\begin{split} V_{DESAT}\big[V\big] &= V_{SCDET} \bullet \frac{R3 + R2}{R3} - V_{F_{D1}} \\ V_{CC2_{MIN}}\big[V\big] &> V_{SCDET} \bullet \frac{R3 + R2 + R1}{R3} \\ t_{BLANKoutemal}\big[s\big] &= -\frac{R2 + R1}{R3 + R2 + R1} \bullet R3 \bullet C_{BLANK} \bullet \ln(1 - \frac{R3 + R2 + R1}{R3} \bullet \frac{V_{SCDET}}{V_{CC2}}) + t_{DESATleb} \end{split}$$

\/		設定参考値	
VDESAT	R1	R2	R3
4.0V	15 kΩ	39kΩ	4.7kΩ
4.5V	15 kΩ	47kΩ	5.1kΩ
5.0V	15 kΩ	51kΩ	5.1kΩ
5.5V	15 kΩ	27kΩ	2.4kΩ
6.0V	15 kΩ	33kΩ	2.7kΩ
6.5V	15 kΩ	62kΩ	4.7kΩ
7.0V	15 kΩ	47kΩ	3.3kΩ
7.5V	15 kΩ	20kΩ	1.3kΩ
8.0V	15 kΩ	82kΩ	5.1kΩ
8.5V	15 kΩ	62kΩ	3.6kΩ
9.0V	15 kΩ	33kΩ	1.8kΩ
9.5V	15 kΩ	75kΩ	3.9kΩ
10.0V	15 kΩ	68kΩ	3.3kΩ

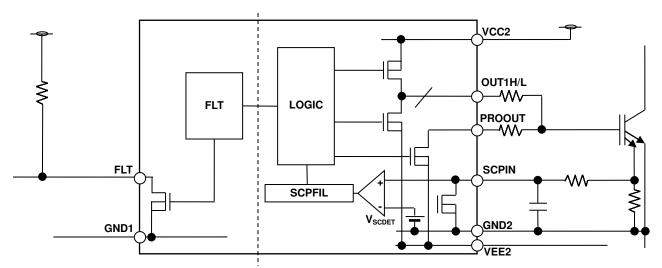


Figure 35. Block Diagram of Short Circuit Protection

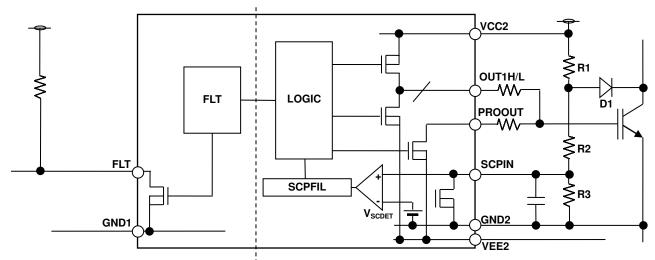


Figure 36. Block Diagram of DESAT

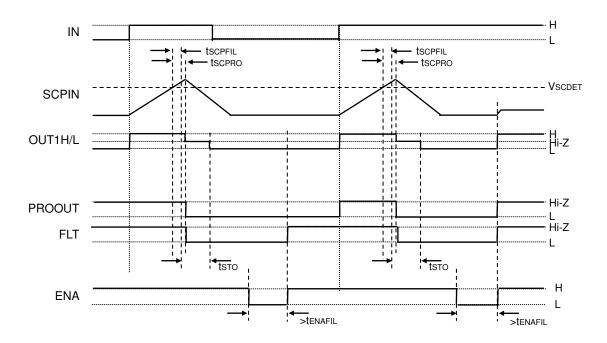


Figure 37. SCP Operation Timing Chart

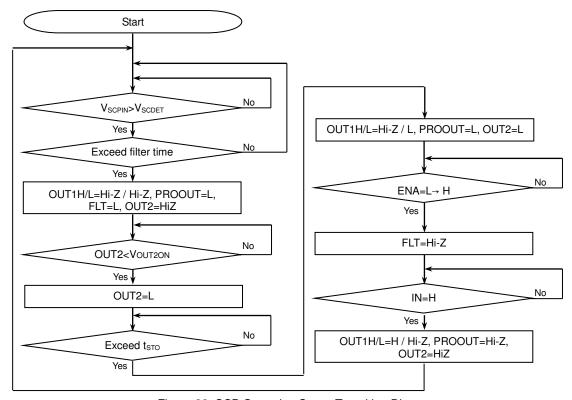


Figure 38. SCP Operation Status Transition Diagram

#### (4) Thermal Protection Function

When the VTSIN pin voltage becomes  $V_{TSDET}$  or less, the thermal protection function will be activated. When the thermal protection function is activated, the OUT1H/L pin voltage will be set to the "Hi-Z/Hi-Z" level and the PROOUT pin voltage will go to the "L" level first (soft turn-OFF). Next, when the VTSIN pin voltage rises to the threshold value and after  $t_{STO}$  has passed, OUT1H/L pin become Hi-Z/L (PROOUT pin hold L). In addition, when OUT2 pin voltage <  $V_{OUT2ON}$ , miller clamp function operates.

When the rising edge is put in the ENA pin, the thermal protection function will be released.

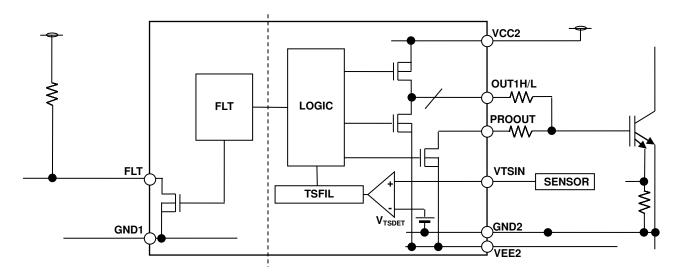


Figure 39. Block Diagram of thermal protection function

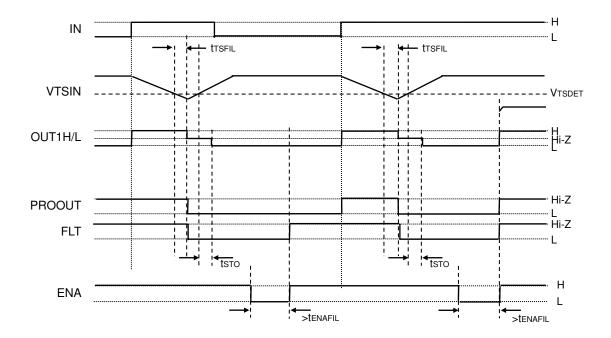


Figure 40. Thermal Protection Function Operation Timing Chart

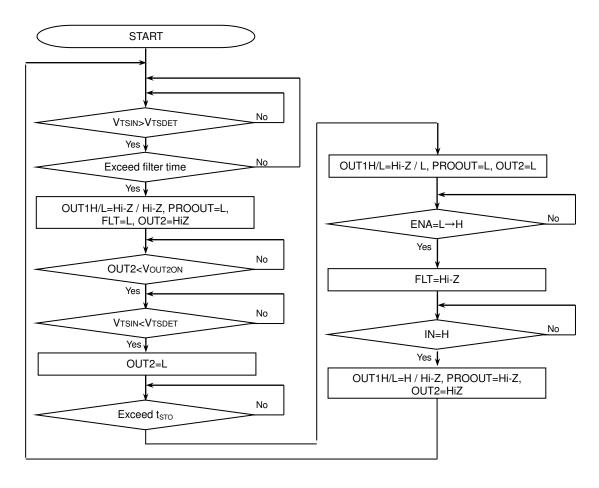


Figure 41. Thermal Protection Function Operation Status Transition Diagram

#### (5) Switching Controller

#### (a) Basic action

This IC has a built-in switching power supply controller which repeats ON/OFF synchronizing with internal clock set by RT pin. When VBATT voltage is supplied (VBATT >  $V_{UVLOBATTH}$ ), FET\_G pin starts switching by soft-start. Output voltage is determined by the following equation by external resistance and winding ratio "n" of flyback transformer (n=  $V_{OUT2}$  side winding number/ $V_{OUT1}$  side winding number)

$$V_{OUT2} = V_{FB} \times \{ (R_1 + R_2)/R_2 \} \times n[V]$$

#### (b) MAX DUTY

When, for example, output load is large, and voltage level of SENSE pin does not reach current detection level, output is forcibly turned OFF by Maximum On Duty (Donmax).

#### (c) Protection function

The switching controller has protection function as overvoltage protection (OVP), under voltage protection (UVP), and over-current protection (OCP). OVP and UVP monitor the voltage of FB pin, OCP monitor the voltage of SENSE pin.

When the protection function is activated, switching controller will be OFF state (FET\_G pin outputs Low). The protection holding time (tdcdcRLs) is completed, the protection function will be released. Under voltage function is not activated during soft-start.

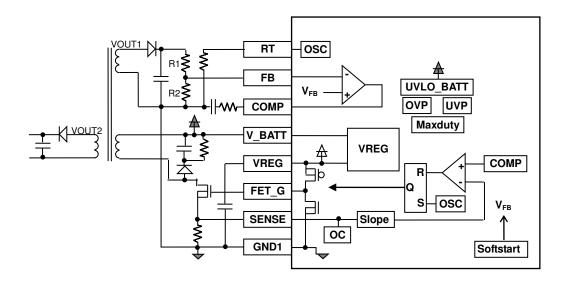


Figure 42. Block Diagram of switching controller

(d)The pin handling when not using switching controller

when not using switching contro	iler, piease do pin nandling as follows.	
pin no.	pin name	

pin no.	pin name	processing method
21	RT	pull down in gnd1 by 68kΩ
22	FB	connect to VREG
23	COMP	connect to VREG
24	V_BATT	connect power supply
25	VREG	connect capacitor
26	FET_G	open
27	SENSE	connect to VREG

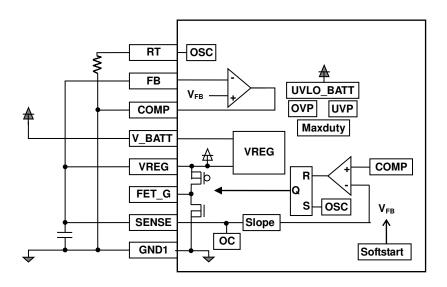


Figure 43. The pin handling when not using switching controller

# (6) Gate State Monitoring Function

When gate logic and input logic of output device monitored with PROOUT pin are compared, a logic L is output from RDY pin when they disaccord. In order to prevent the detection error due to delay of input and output, OSFB filter time tosfbril is provided.

(7)	(7) I/O Condition Table															
			Input							Output						
No.	Status	V B A T T	V C C 2	S C P I N	V T S I N	E N A	I N B	I N A	O U T 2	P R O O U T	O U T 1 H	O U T 1 L	O U T 2	P R O O U T	F L T	R D Y
1	SCP	0	0	Н	Н	Н	L	Н	Н	Χ	Hi-Z	Hi-Z	Hi-Z	L	L	Hi-Z
2	30P	0	0	Н	Н	Н	L	Н	L	Х	Hi-Z	Hi-Z	L	L	L	Hi-Z
3	UVLO_VBATT	UVLO	0	L	Ι	Х	Χ	Χ	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
4	UVLO_VBATT	UVLO	0	L	Н	Х	Х	Χ	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	L
5	UVLO VCC2	0	UVLO	┙	Ι	Х	Χ	Χ	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
6		0	UVLO	L	Ι	Х	Χ	Χ	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	L
7	Thermal	0	0	L	L	Χ	Χ	Χ	Н	Χ	Hi-Z	Hi-Z	Hi-Z	L	L	Hi-Z
8	protection	0	0	┙	L	Х	Х	Χ	L	Х	Hi-Z	Hi-Z	Ш	L	L	Hi-Z
9	Disable	0	0	L	Н	L	Х	Χ	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
10	Disable	0	0	L	Ι	L	Χ	Χ	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
11	INB active	0	0	┙	Ι	Н	Н	Χ	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
12	12	0	0	L	Ι	Н	Н	Χ	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
13	Normal Operation	0	0	L	Η	Н	L	L	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
14		0	0	L	Η	Н	L	L	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
15	Normal Operation	0	0	L	Η	Н	L	Н	Н	Н	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z
16	H Input	0	0	L	Н	Н	L	Н	L	L	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z	L

o: > UVLO, X:Don't care

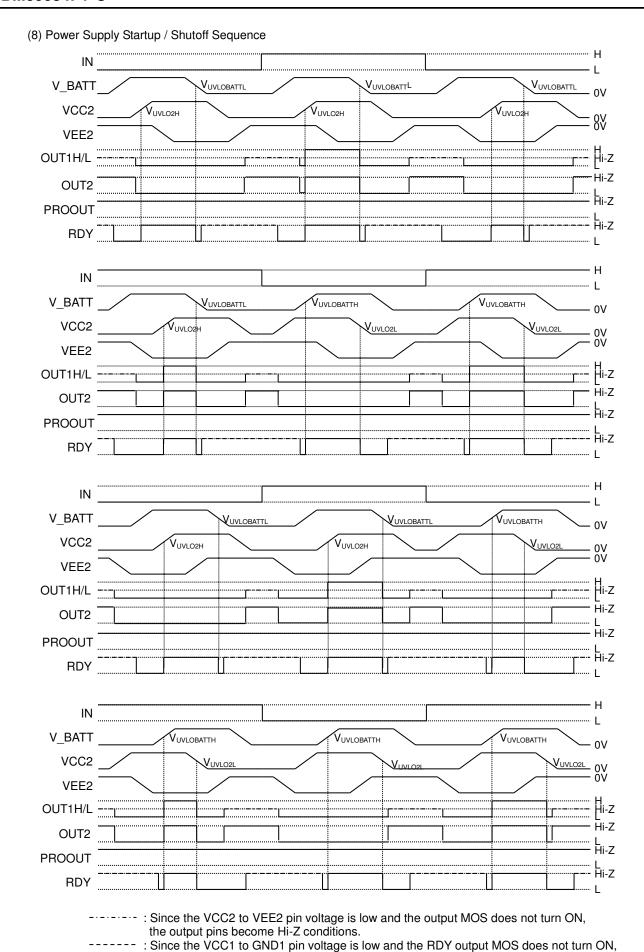
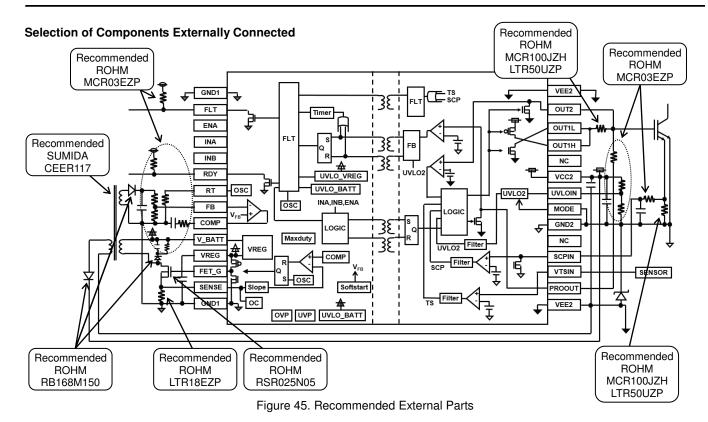


Figure 44. Power Supply Startup / Shutoff Sequence

the output pins become Hi-Z conditions.



### **Power Dissipation**

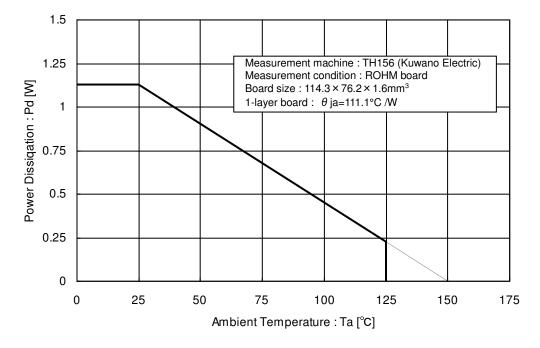


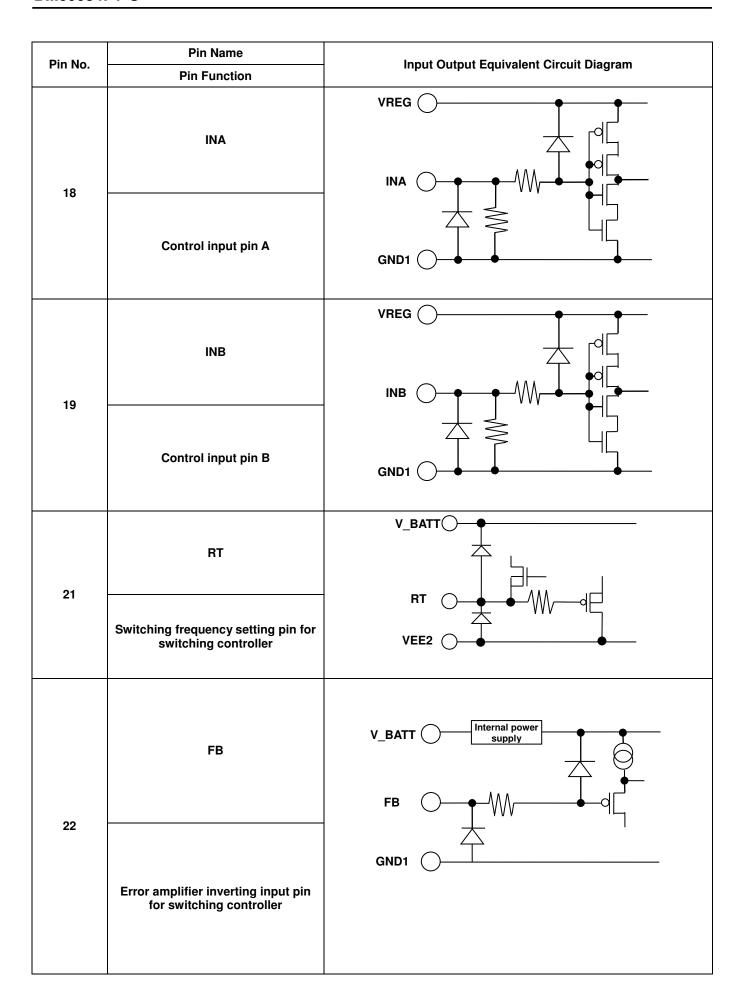
Figure 46. SSOP-B28W Derating Curve

# **Thermal Design**

Please make sure that the IC's chip temperature Tj is not over 150°C, while considering the IC's power consumption (W), package power (Pd) and ambient temperature (Ta). When Tj=150°C is exceeded, the IC may malfunctions or some problems (ex. abnormal operation of various parasitic elements and increasing of leak current) may occur. Constant use under these circumstances leads to deterioration and eventually IC may destruct. Tjmax=150°C must be strictly obeyed under all circumstances.

/O Equivalence Circuits							
Pin No.	Pin Name	Input Output Equivalent Circuit Diagram					
1 111 140.	Pin Function	mpat Garpat Equitation, Ground England					
2	PROOUT	VCC2 PROOUT					
	Soft turn-off pin / Gate voltage input pin	VEE2					
3	VTSIN	VCC2					
	Thermal detection pin	GND2					
4	SCPIN	VCC2					
	Schort circuit current detection pin	SCPIN GND2					
7	MODE	VCC2  MODE					
	Mode selection pin of output-side UVLO	GND2 VEE2					
•	UVLOIN	VCC2					
8	Output-side UVLO setting pin	GND2 VEE2					

Pin No.	Pin Name	Input Output Equivalent Circuit Diagram				
	Pin Function					
	ОПТ1Н	—_ <b>♦</b> → ○ VCC2				
11	Source side output pin	OUT1L				
12	OUT1L	VEE2				
	Sink side output pin					
13	OUT2	VCC2				
	Output pin for Miller Clamp	VEE2				
	FLT					
16	Fault output pin	FLT RDY				
	RDY					
20	Ready output pin	——————————————————————————————————————				
	ENA	VREG				
		ENA O				
17	Input enabling signal pin	GND1				



Pin No.	Pin Name	Input Output Equivalent Circuit Diagram				
Pin No.	Pin Function	input Output Equivalent Offcult Diagram				
23	СОМР	V_BATT Internal power supply  COMP				
	Error amplifier output pin for switching controller	GND1 GND1				
25	VREG	Internal power V_BATT				
25	Input-side internal power supply pin	vreg				
	FET_G	FET_G				
26	MOS FET control pin for switching controller	GND1				
0.7	SENSE	V_BATT Internal power supply				
27	Current detection pin for switching controller	SENSE				

# **Operational Notes**

#### 1. Reverse Connection of Power Supply

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

# 2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

#### 3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

#### 4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

#### 5. Thermal Consideration

Should by any chance the power dissipation rating be exceeded, the rise in temperature of the chip may result in deterioration of the properties of the chip. The absolute maximum rating of the Pd stated in this specification is when the IC is mounted on a 70mm x 70mm x 1.6mm glass epoxy board. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the Pd rating.

#### 6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IC can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

#### 7. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

#### 8. Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

# 9. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

# 10. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

# 11. Unused Input Terminals

Input terminals of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input terminals should be connected to the power supply or ground line.

# **Operational Notes - continued**

#### 12. Regarding Input Pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode.

When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

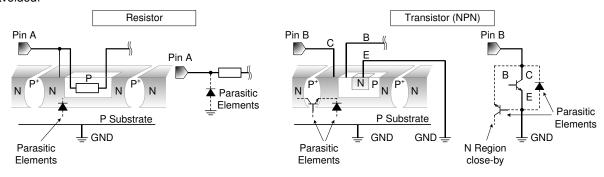
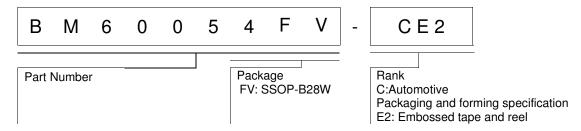


Figure 47. Example of Monolithic IC Structure

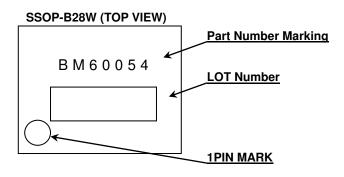
#### 13. Ceramic Capacitor

When using a ceramic capacitor, determine the dielectric constant considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

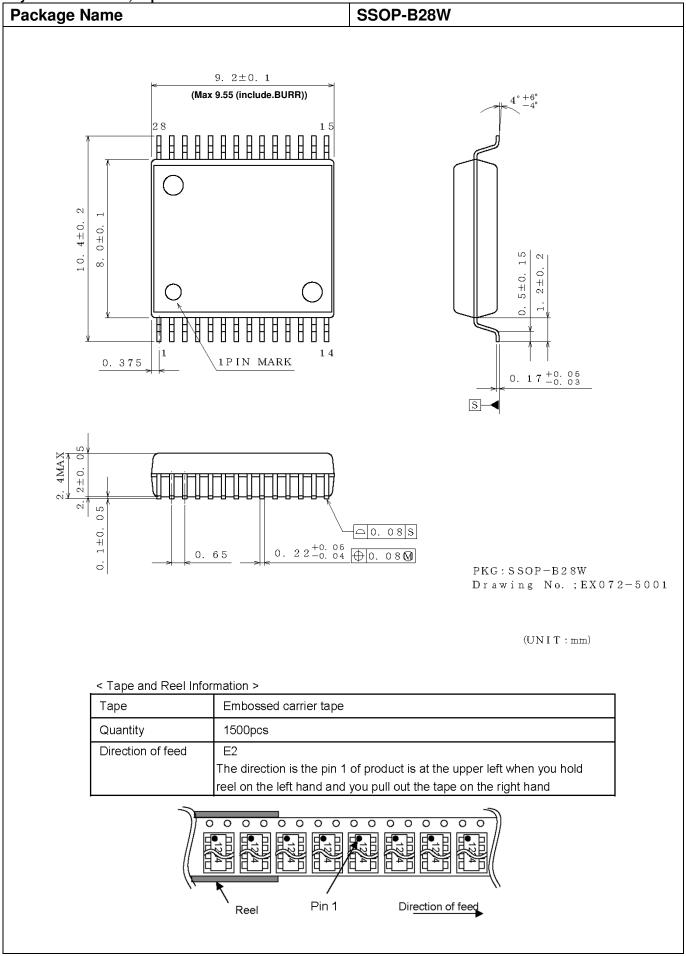
### **Ordering Information**



# **Marking Diagram**



Physical Dimension, Tape and Reel Information



# **Revision History**

Date	Revision	Changes			
10.Apr.2015	001	New Release			
25.Dec.2015	002	Page 7 Adding UL1577 Rating Table Page15 Misprint correction of Description of Pins and Cautions on Layout of Board (7)FLT Page17 Misprint correction of Description of Functions and Examples of Constant Setting (1)Miller Clamp Function			

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ĺ	JAPAN	USA	FU	CHINA
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	CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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